

Shinya Yamada

List of Publications by Year in descending order

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138
times ranked

1149
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Room-temperature generation of giant pure spin currents using epitaxial Co ₂ FeSi spin injectors. NPC Asia Materials, 2012, 4, e9-e9. | 3.8 | 86 |
| 2 | Estimation of the spin polarization for Heusler-compound thin films by means of nonlocal spin-valve measurements: Comparison of Co ₂ FeSi and Fe ₃ Si. Physical Review B, 2012, 85, . | 1.1 | 81 |
| 3 | Significant growth-temperature dependence of ferromagnetic properties for Co ₂ FeSi/Si(111) prepared by low-temperature molecular beam epitaxy. Applied Physics Letters, 2010, 96, . | 1.5 | 65 |
| 4 | Greatly enhanced generation efficiency of pure spin currents in Ge using Heusler compound Co ₂ FeSi electrodes. Applied Physics Express, 2014, 7, 033002. | 1.1 | 65 |
| 5 | Spin accumulation created electrically in an <i>n</i> -type germanium channel using Schottky tunnel contacts. Journal of Applied Physics, 2012, 111, . | 1.1 | 62 |
| 6 | Electric-field control of spin accumulation signals in silicon at room temperature. Applied Physics Letters, 2011, 99, 132511. | 1.5 | 56 |
| 7 | Spin Transport and Relaxation up to 250K in Heavily Doped <i>n</i> -Type Ge Detected Using Local Structural Ordering in low-temperature-grown epitaxial Fe ₃ Si. Applied Physics Letters, 2012, 101, 162401. | 1.5 | 52 |
| 8 | Room-temperature structural ordering of a Heusler compound Fe ₃ Si. Physical Review B, 2012, 86, . | 1.1 | 48 |
| 9 | Spin transport and relaxation in germanium. Journal Physics D: Applied Physics, 2018, 51, 393001. | 1.3 | 48 |
| 11 | Giant Spin Accumulation in Silicon Nonlocal Spin-Transport Devices. Physical Review Applied, 2017, 8, . | 1.5 | 47 |
| 12 | Highly ordered Co ₂ FeSi Heusler alloys grown on Ge(111) by low-temperature molecular beam epitaxy. Journal of Applied Physics, 2010, 107, . | 1.1 | 44 |
| 13 | Electrical properties of pseudo-single-crystalline germanium thin-film-transistors fabricated on glass substrates. Applied Physics Letters, 2015, 107, . | 1.5 | 44 |
| 14 | A pseudo-single-crystalline germanium film for flexible electronics. Applied Physics Letters, 2015, 106, . | 1.5 | 44 |
| 15 | Dynamical Spin Injection into p-Type Germanium at Room Temperature. Applied Physics Express, 2013, 6, 023001. | 1.1 | 39 |
| 16 | Atomically Controlled Epitaxial Growth of Single-Crystalline Germanium Films on a Metallic Silicide. Crystal Growth and Design, 2012, 12, 4703-4707. | 1.4 | 37 |
| 17 | Qualitative study of temperature-dependent spin signals in <i>n</i> -Ge-based lateral devices with Fe ₃ Si/ <i>n</i> -Ge Schottky-tunnel contacts. Journal of Applied Physics, 2013, 113, . | 1.1 | 34 |
| 18 | Improvement of magnetic and structural stabilities in high-quality Co ₂ FeSi _{1-x} Al _x /Si heterointerfaces. Applied Physics Letters, 2014, 105, . | 1.5 | 34 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | Giant enhancement of spin pumping efficiency using Fe ₃ Si ferromagnet. Physical Review B, 2013, 88, . | 1.1 | 33 |
| 20 | Mechanism of Fermi level pinning at metal/germanium interfaces. Physical Review B, 2011, 84, . | 1.1 | 32 |
| 21 | Spin injection through energy-band symmetry matching with high spin polarization in atomically controlled ferromagnet/ferromagnet/semiconductor structures. NPC Asia Materials, 2020, 12, . | 3.8 | 32 |
| 22 | Temperature evolution of spin accumulation detected electrically in a nondegenerated silicon channel. Physical Review B, 2012, 85, . | 1.1 | 31 |
| 23 | Site-selective nanoscale-polymerization of pyrrole on gold nanoparticles via plasmon induced charge separation. Nanoscale, 2016, 8, 8520-8524. | 2.8 | 31 |
| 24 | Room-temperature spin transport in n-Ge probed by four-terminal nonlocal measurements. Applied Physics Express, 2017, 10, 093001. | 1.1 | 31 |
| 25 | Temperature-independent spin relaxation in heavily doped n-type germanium. Physical Review B, 2016, 94, . | 1.1 | 30 |
| 26 | High-quality epitaxial CoFe/Si(111) heterostructures fabricated by low-temperature molecular beam epitaxy. Applied Physics Letters, 2010, 97, . | 1.5 | 28 |
| 27 | Low-temperature grown quaternary Heusler-compound Co ₂ Mn _{1-x} Fe _x Si films on Ge(111). Journal of Applied Physics, 2011, 109, 07B113. | 1.1 | 25 |
| 28 | Photoinduced intramolecular electron-transfer reactions in carbazole-fullerene and phenothiazine-fullerene linked compounds in benzene and benzonitrile as studied by fluorescence, transient absorption, time-resolved EPR, and magnetic field effects. Applied Magnetic Resonance, 2003, 23, 289-307. | 0.6 | 24 |
| 29 | Electrical properties of pseudo-single-crystalline Ge films grown by Au-induced layer exchange crystallization at 250°C. Journal of Applied Physics, 2018, 123, 215704. | 1.1 | 24 |
| 30 | Spin transport in p-Ge through a vertically stacked Ge/Fe ₃ Si junction. Applied Physics Letters, 2016, 109, . | 1.5 | 23 |
| 31 | An ultra-thin buffer layer for Ge epitaxial layers on Si. Applied Physics Letters, 2013, 102, . | 1.5 | 22 |
| 32 | Large impact of impurity concentration on spin transport in degenerate n-Ge. Physical Review B, 2017, 95, . | 1.1 | 22 |
| 33 | Anomalous Hall conductivity and electronic structures of Si-substituted Mn ₂ Ge epitaxial films. Physical Review B, 2018, 97, . | | |
| 34 | Nonlinear Electrical Spin Conversion in a Biased Ferromagnetic Tunnel Contact. Physical Review Applied, 2018, 10, . | 1.5 | 21 |
| 35 | Room-temperature detection of spin accumulation in silicon across Schottky tunnel barriers using a metal-oxide-semiconductor field effect transistor structure (invited). Journal of Applied Physics, 2013, 113, . | 1.1 | 20 |
| 36 | A crystalline germanium flexible thin-film transistor. Applied Physics Letters, 2017, 111, . | 1.5 | 20 |

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|----|--|-----|-----------|
| 37 | Epitaxial growth of a full-Heusler alloy Co ₂ FeSi on silicon by low-temperature molecular beam epitaxy. Thin Solid Films, 2010, 518, S278-S280. | 0.8 | 19 |
| 38 | Effect of Addition of Al to Single-Crystalline CoFe Electrodes on Nonlocal Spin Signals in Lateral Spin-Valve Devices. Applied Physics Express, 2012, 5, 063004. | 1.1 | 18 |
| 39 | Large anisotropy of Gilbert damping constant in L ₂ -ordered Co ₂ FeSi film. Applied Physics Express, 2014, 7, 123001. | 1.1 | 18 |
| 40 | High-quality Co ₂ FeSi _{0.5} Al _{0.5} /Si heterostructures for spin injection in silicon spintronic devices. Thin Solid Films, 2014, 557, 390-393. | 0.8 | 18 |
| 41 | Realisation of magnetically and atomically abrupt half-metal/semiconductor interface: Co ₂ FeSi _{0.5} Al _{0.5} /Ge(111). Scientific Reports, 2016, 6, 37282. | 1.6 | 18 |
| 42 | Pure spin current transport in a SiGe alloy. Applied Physics Express, 2018, 11, 053006. | 1.1 | 18 |
| 43 | All-epitaxial Co ₂ FeSi/Ge/Co ₂ FeSi trilayers fabricated by Sn-induced low-temperature epitaxy. Journal of Applied Physics, 2016, 119, . | 1.1 | 17 |
| 44 | Direct evidence for suppression of the Kondo effect due to pure spin current. Physical Review B, 2016, 94, . | 1.1 | 17 |
| 45 | Low-temperature growth of fully epitaxial CoFe/Ge/Fe ₃ Si layers on Si for vertical-type semiconductor spintronic devices. Semiconductor Science and Technology, 2017, 32, 094005. | 1.0 | 17 |
| 46 | Magnetic and transport properties of equiatomic quaternary Heusler CoFeVSi epitaxial films. Physical Review Materials, 2018, 2, . | 0.9 | 17 |
| 47 | Room-temperature two-terminal magnetoresistance ratio reaching 0.1% in semiconductor-based lateral devices with L ₂₁ -ordered Co ₂ MnSi. Applied Physics Letters, 2021, 118, . | 1.5 | 16 |
| 48 | Electrical detection of spin accumulation and relaxation in p-type germanium. Physical Review Materials, 2017, 1, . | 0.9 | 16 |
| 49 | Magnetic field effects on photoelectrochemical reactions of modified electrodes with C ₆₀ -phenothiazine nanoclusters. Science and Technology of Advanced Materials, 2006, 7, 643-648. | 2.8 | 15 |
| 50 | The role of chemical structure on the magnetic and electronic properties of Co ₂ FeAl _{0.5} Si _{0.5} /Si(111) interface. Applied Physics Letters, 2016, 108, . | 1.5 | 15 |
| 51 | Spin injection into multilayer graphene from highly spin-polarized Co ₂ FeSi Heusler alloy. Applied Physics Express, 2016, 9, 063006. | 1.1 | 15 |
| 52 | Correlation between spin transport signal and Heusler/semiconductor interface quality in lateral spin-valve devices. Physical Review B, 2018, 98, . | 1.1 | 15 |
| 53 | Significant reduction in the thermal conductivity of Si-substituted Fe ₂ epilayers. Physical Review B, 2019, 99, . | | |
| 54 | Positive linear magnetoresistance effect in disordered L ₂ -type Mn ₂ epitaxial films. Physical Review B, 2021, 103, . | 1.1 | 15 |

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|----|--|-----|-----------|
| 55 | Room-temperature sign reversed spin accumulation signals in silicon-based devices using an atomically smooth Fe ₃ Si/Si(111) contact. Journal of Applied Physics, 2013, 113, . | 1.1 | 14 |
| 56 | Effect of Co-Fe substitution on room-temperature spin polarization in Co ₃ Fe _{1-x} Si _x Heusler-compound films. Physical Review B, 2013, 88, . | 1.1 | 14 |
| 57 | Lateral spin valves with two-different Heusler-alloy electrodes on the same platform. Applied Physics Letters, 2013, 103, . | 1.5 | 14 |
| 58 | Molecular Beam Epitaxy of Co ₂ MnSi Films on Group-IV Semiconductors. Japanese Journal of Applied Physics, 2013, 52, 04CM06. | 0.8 | 14 |
| 59 | Finely Controlled Approaches to Formation of Heusler-Alloy/Semiconductor Heterostructures for Spintronics. Materials Transactions, 2016, 57, 760-766. | 0.4 | 14 |
| 60 | Nonmonotonic bias dependence of local spin accumulation signals in ferromagnet/semiconductor lateral spin-valve devices. Physical Review B, 2019, 100, . | 1.1 | 14 |
| 61 | Manipulator control by using servoing with the stereo vision. , 0, , . | | 13 |
| 62 | Reliable reduction of Fermi-level pinning at atomically matched metal/Ge interfaces by sulfur treatment. Applied Physics Letters, 2014, 104, 172109. | 1.5 | 13 |
| 63 | Suppression of Donor-Driven Spin Relaxation in Strained Si _{0.1} Ge _{0.9} Channel. Physical Review Applied, 2020, 13, . | 1.5 | 13 |
| 64 | Giant converse magnetoelectric effect in a multiferroic heterostructure with polycrystalline Co ₂ FeSi. NPC Asia Materials, 2022, 14, . | 3.8 | 13 |
| 65 | Influence of Al co-deposition on the crystal growth of Co-based Heusler-compound thin films on Si(111). Thin Solid Films, 2012, 520, 3419-3422. | 0.8 | 12 |
| 66 | Spin-related thermoelectric conversion in lateral spin-valve devices with single-crystalline Co ₂ FeSi electrodes. Applied Physics Express, 2015, 8, 043003. | 1.1 | 12 |
| 67 | Observation of micro-cracks beneath fracture surface during dynamic crack propagation. Theoretical and Applied Fracture Mechanics, 2017, 92, 178-184. | 2.1 | 12 |
| 68 | Low thermal conductivity of thermoelectric Fe ₂ VAI films. Applied Physics Express, 2017, 10, 115802. | 1.1 | 12 |
| 69 | Control of electrical properties in Heusler-alloy/Ge Schottky tunnel contacts by using phosphorous $\hat{\Gamma}$ -doping with Si-layer insertion. Materials Science in Semiconductor Processing, 2017, 70, 83-85. | 1.9 | 12 |
| 70 | Observation of local magnetoresistance signals in a SiGe-based lateral spin-valve device. Semiconductor Science and Technology, 2018, 33, 114009. | 1.0 | 12 |
| 71 | Quantification of Spin Drift in Devices with a Heavily Doped Si Channel. Physical Review Applied, 2019, 11, . | 1.5 | 12 |
| 72 | Thermoelectric properties of single-phase full-Heusler alloy Fe ₂ TiSi films with <i>D</i> ₃ -type disordering. Journal of Applied Physics, 2020, 127, . | 1.1 | 12 |

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|----|---|-----|-----------|
| 73 | Room-temperature local magnetoresistance effect in i -Ge devices with low-resistive Schottky-tunnel contacts. Applied Physics Express, 2019, 12, 033002. | 1.1 | 11 |
| 74 | Room-Temperature Tunneling Magnetoresistance in Magnetic Tunnel Junctions with a $\text{DO}_3\text{-Fe}_3\text{Si}$ Electrode. Japanese Journal of Applied Physics, 2013, 52, 04CM02. | 0.8 | 10 |
| 75 | Formation of Ge(111) on Insulator by Ge epitaxy on Si(111) and layer transfer. Thin Solid Films, 2014, 557, 76-79. | 0.8 | 10 |
| 76 | Effect of annealing on the structure and magnetic properties of $\text{Co}_2\text{FeAl}_{0.5}\text{Si}_{0.5}$ thin films on Ge(111). Journal of Alloys and Compounds, 2018, 748, 323-327. | 2.8 | 10 |
| 77 | Great Differences between Low-Temperature Grown Co_2FeSi and Co_2MnSi Films on Single-Crystalline Oxides. ACS Applied Electronic Materials, 2019, 1, 2371-2379. | 2.0 | 10 |
| 78 | Hanle spin precession in a two-terminal lateral spin valve. Applied Physics Letters, 2019, 114, 242401. | 1.5 | 10 |
| 79 | Electric field tunable anisotropic magnetoresistance effect in an epitaxial $\text{CoO}_3\text{-Fe}_3\text{Si}$ interfacial multiferroic system. Physical Review Materials, 2021, 5, . | 0.9 | 10 |
| 80 | Facile oxidation of thiophenol by a flavin immobilized in cationic polyelectrolytes: A flavoenzyme model. Journal of Polymer Science, Polymer Letters Edition, 1978, 16, 137-140. | 0.4 | 9 |
| 81 | Influence of the Ge diffusion on the magnetic and structural properties in Fe_3Si and CoFe epilayers grown on Ge. Journal of Crystal Growth, 2017, 468, 676-679. | 0.7 | 9 |
| 82 | Effect of $\text{Fe}\delta\text{-V}$ nonstoichiometry on electrical and thermoelectric properties of Fe_2VAl films. Japanese Journal of Applied Physics, 2018, 57, 040306. | 0.8 | 9 |
| 83 | Experimental verification of the origin of positive linear magnetoresistance in CoFeMo Heusler alloys. Physical Review B, 2019, 100, . | 1.1 | 9 |
| 84 | Direct observation of pseudo-gap electronic structure in the Heusler-type Fe_2VAl thin film. Journal of Electron Spectroscopy and Related Phenomena, 2019, 232, 1-4. | 0.8 | 9 |
| 85 | Giant magnetoelectric effect in an L_{21} -ordered $\text{Co}_2\text{FeSi/Pb}(\text{Mg}_{1/3}\text{Nb}_{2/3})\text{O}_3\text{-PbTiO}_3$ multiferroic heterostructure. Applied Physics Letters, 2021, 118, . | 1.5 | 9 |
| 86 | Sign determination of spin polarization in L_{21} -ordered Co_2FeSi multiferroic heterostructure. Applied Physics Letters, 2021, 118, . | 1.1 | 8 |
| 87 | Low-temperature epitaxial Fe_3Si and magnetic properties of Co_2FeSi using a Pt-based spin Hall device. Physical Review B, 2015, 92, . | 1.1 | 8 |
| 88 | Electrical properties of epitaxial Lu- or Y-doped $\text{La}_2\text{O}_3/\text{La}_2\text{O}_3/\text{Ge}$ high- k gate-stacks. Materials Science in Semiconductor Processing, 2017, 70, 260-264. | 1.9 | 8 |
| 89 | Half-metallic nature of the low-temperature grown Co_2MnSi films on SrTiO_3 . Journal of Alloys and Compounds, 2021, 854, 155571. | 2.8 | 8 |
| 90 | Magnetoresistance ratio of more than 1% at room temperature in germanium vertical spin-valve devices with Co_2FeSi . Applied Physics Letters, 2021, 119, . | 1.5 | 8 |

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|-----|--|-----|-----------|
| 91 | Construction of a consulting system from structural description of a mechanical object. , 0, , . | | 7 |
| 92 | A magnetic tunnel junction with an L21-ordered Co ₂ FeSi electrode formed by all room-temperature fabrication processes. Thin Solid Films, 2014, 557, 386-389. | 0.8 | 7 |
| 93 | Effect of the magnetic domain structure in the ferromagnetic contact on spin accumulation in silicon. Applied Physics Letters, 2012, 101, 232404. | 1.5 | 6 |
| 94 | Room-temperature electrical creation of spin accumulation in n-Ge using highly resistive Fe ₃ Si/n+-Ge Schottky-tunnel contacts. Thin Solid Films, 2014, 557, 382-385. | 0.8 | 6 |
| 95 | Effect of atomic-arrangement matching on La ₂ O ₃ /Ge heterostructures for epitaxial high-k-gate-stacks. Journal of Applied Physics, 2015, 118, . | 1.1 | 6 |
| 96 | Inner Approximation Method for a Reverse Convex Programming Problem. Journal of Optimization Theory and Applications, 2000, 107, 355-389. | 0.8 | 5 |
| 97 | Epitaxial growth of Sb-doped Ge layers on ferromagnetic Fe ₃ Si for vertical semiconductor spintronic devices. Semiconductor Science and Technology, 2018, 33, 104008. | 1.0 | 5 |
| 98 | Proximity exchange coupling in a Fe/MgO/Si tunnel contact detected by the inverted Hanle effect. Physical Review B, 2019, 100, . | 1.1 | 5 |
| 99 | Control of thermoelectric properties in Mn-substituted $\text{Fe}_{1-x}\text{Mn}_x\text{Si}$ epilayers. Physical Review B, 2020, 102, . | | |
| 100 | Effect of Fe atomic layers at the ferromagnet-semiconductor interface on temperature-dependent spin transport in semiconductors. Journal of Applied Physics, 2021, 129, . | 1.1 | 5 |
| 101 | Effect of an Atomically Matched Structure on Fermi-level Pinning at Metal/p-Ge Interfaces. ECS Transactions, 2013, 50, 223-229. | 0.3 | 4 |
| 102 | An All-Epitaxial Fe ₃ Si/Co ₂ FeSi Trilayer Grown by Room-Temperature Molecular Beam Epitaxy. IEEE Transactions on Magnetics, 2014, 50, 1-3. | 1.2 | 4 |
| 103 | Exchange coupling in metallic multilayers with a top FeRh layer. AIP Advances, 2016, 6, . | 0.6 | 4 |
| 104 | Magnetic properties and interfacial characteristics of all-epitaxial Heusler-compound stacking structures. Physical Review B, 2016, 94, . | 1.1 | 4 |
| 105 | Spin transport in antimony-doped germanium detected using vertical spin-valve structures. Applied Physics Express, 2020, 13, 023001. | 1.1 | 4 |
| 106 | Uniaxially strained SiGe(111) and SiGe(100) grown on selectively ion-implanted substrates. Journal of Crystal Growth, 2014, 401, 758-761. | 0.7 | 3 |
| 107 | Controlling the half-metallicity of Heusler/Si(111) interfaces by a monolayer of SiCoSi. Journal of Physics Condensed Matter, 2016, 28, 395003. | 0.7 | 3 |
| 108 | A low-temperature fabricated gate-stack structure for Ge-based MOSFET with ferromagnetic epitaxial Heusler-alloy/Ge electrodes. Japanese Journal of Applied Physics, 2016, 55, 063001. | 0.8 | 3 |

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|-----|--|-----|-----------|
| 109 | Magnetic and structural depth profiles of Heusler alloy $\text{Co}_{2-x}\text{FeAl}_{0.5-x}\text{Si}_{0.5-x}$ epitaxial films on Si(100). Journal of Physics Condensed Matter, 2018, 30, 065801. | 0.7 | 3 |
| 110 | Germanium pn junctions between ferromagnetic CoFe and Fe ₃ Si layers for spintronic applications. Materials Science in Semiconductor Processing, 2020, 116, 105066. | 1.9 | 3 |
| 111 | Substrate dependent reduction of Gilbert damping in annealed Heusler alloy thin films grown on group IV semiconductors. Applied Physics Letters, 2021, 119, . | 1.5 | 3 |
| 112 | Superimposed contributions to two-terminal and nonlocal spin signals in lateral spin-transport devices. Physical Review B, 2021, 104, . | 1.1 | 3 |
| 113 | Converse Magnetoelectric Effect in Epitaxial $\text{Co}_{1-x}\text{MnSi}/\text{Pb}(\text{Mg}_{1/3}\text{Nb}_{2/3})\text{O}_f$ - PbTiO_f Multiferroic Heterostructures. IEEE Transactions on Magnetics, 2022, 58, 1-5. | 1.2 | 3 |
| 114 | Robust spin-current injection in lateral spin valves with two-terminal Co_2FeSi spin injectors. AIP Advances, 2017, 7, 055808. | 0.6 | 2 |
| 115 | Inverse local magnetoresistance effect up to room temperature in ferromagnet-semiconductor lateral spin-valve devices. Materials Science in Semiconductor Processing, 2020, 113, 105046. | 1.9 | 2 |
| 116 | Structural insight using anomalous XRD into Mn_2CoAl Heusler alloy films grown by magnetron sputtering, IBAS, and MBE techniques. Acta Materialia, 2022, 235, 118063. | 3.8 | 2 |
| 117 | An inner approximation method for a reverse convex programming problem. , 0, , . | | 1 |
| 118 | Mid-infrared pulsed laser lithotripsy using an Er:YAG laser and a difference frequency generation laser. Proceedings of SPIE, 2008, , . | 0.8 | 1 |
| 119 | Validation of stepwise refinement with test cases generated from formal specification. , 2010, , . | | 1 |
| 120 | High-quality ferromagnetic CoFe/Si contacts for Si spin-transistor applications. , 2010, , . | | 1 |
| 121 | Generation and Detection of a Pure Spin Current Using Co-Based Heusler-Alloy Spin Injector and Detector: Comparison of Co_2MnSi and Co_2FeSi . ECS Transactions, 2013, 50, 245-251. | 0.3 | 1 |
| 122 | Spin Absorption Effect at Ferromagnet/Ge Schottky-Tunnel Contacts. Materials, 2018, 11, 150. | 1.3 | 1 |
| 123 | Modulation of magnetization dynamics in an epitaxial Heusler ferromagnet due to pure spin current in a laterally configured structure. Journal of Physics Condensed Matter, 2018, 30, 255802. | 0.7 | 1 |
| 124 | Magnetic and Transport Properties of $\text{Co}_{1-x}\text{Fe}_x\text{Si}$ Epitaxial Films Grown by Molecular Beam Epitaxy. IEEE Transactions on Magnetics, 2019, 55, 1-4. | 1.2 | 1 |
| 125 | Growth of ferromagnetic Co_2FeSi films on flexible Ge(111). Materials Science in Semiconductor Processing, 2020, 112, 104997. | 1.9 | 1 |
| 126 | Experimental estimation of the spin diffusion length in undoped p-Ge on Fe ₃ Si using vertical spin-valve devices. Journal of Applied Physics, 2021, 129, 013901. | 1.1 | 1 |

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|-----|---|-----|-----------|
| 127 | Spin signals in Si non-local transport devices with giant spin accumulation. , 2017, , . | | 1 |
| 128 | A novel laser angioplasty guided hollow fiber using mid-infrared laser. , 2006, , . | | 0 |
| 129 | Ferromagnetic Co ₃ Fe/Si/Si(111) contacts with high-quality heterointerfaces for spin-transistor applications. , 2010, , . | | 0 |
| 130 | (Invited) SiGe Spintronics with Single-Crystalline Ferromagnetic Schottky-Tunnel Contacts. ECS Transactions, 2013, 50, 235-243. | 0.3 | 0 |
| 131 | Ion beam analysis of quaternary Heusler alloy Co ₂ (Mn ¹⁺ Fe ^x)Si(111) epitaxially grown on Ge(111). Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1828-1831. | 0.8 | 0 |
| 132 | Effect of Sn-doped Ge insertion layers on epitaxial growth of ferromagnetic Fe ₃ Si films on a flexible substrate. , 2014, , . | | 0 |
| 133 | Low-temperature Grown Ge ₁ Sn _x layers on a metallic silicide. , 2014, , . | | 0 |
| 134 | Atomically controlled heteroepitaxy of Ge on a ferromagnetic heusler alloy for a vertical-type spin transistor. , 2014, , . | | 0 |
| 135 | Atomic and electronic structure study of a Co ₂ FeAl _{0.5} Si _{0.5} half-metal thin film on Si(111). Microscopy and Microanalysis, 2016, 22, 1524-1525. | 0.2 | 0 |
| 136 | (Invited) Finely Controlled Heterointerfaces between Ge(111) and Metallic Alloys or Insulators for Next Generation Ge-Based Devices. ECS Transactions, 2016, 75, 651-659. | 0.3 | 0 |
| 137 | Epitaxial Mn ₂ VAI films with structure for all-Heusler stacks. Journal of Magnetism and Magnetic Materials, 2022, , 169644. | 1.0 | 0 |